

Product features

Mature GaAs processing technology,
50 Ω coplanar waveguide output, gold wire bonding.

Main specifications

Parameters	Frequency	/	Min	Typical	Max	Units
Passband	/	/	1700	~	1900	MHz
Center loss	/	/			3.5	dB
Ripple	/	/			1.2	dB
Rejection	1300	MHz $\geq$	48			dBc
Rejection	2300	MHz $\geq$	34			dBc
Passband VSWR	/	/			1.6	

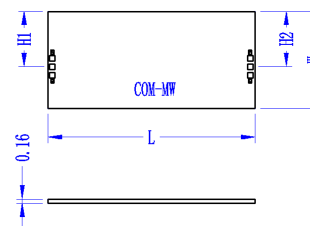
Other parameters

Connector	Microstrip pad
Impedance	50 Ω
Power Capacity	25dBm Design assurance
Operation Temp.	-55~+125°C Design assurance
Storage Temp.	-65~+150°C Design assurance
Quality Grade	Industrial grade
ROHS	Compliant Available
Filter Category	MMIC

Reference picture

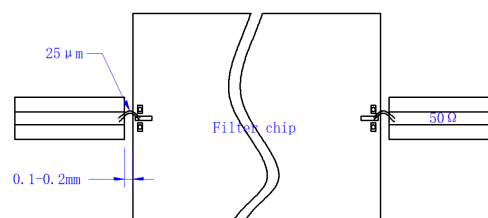


Configuration(mm)

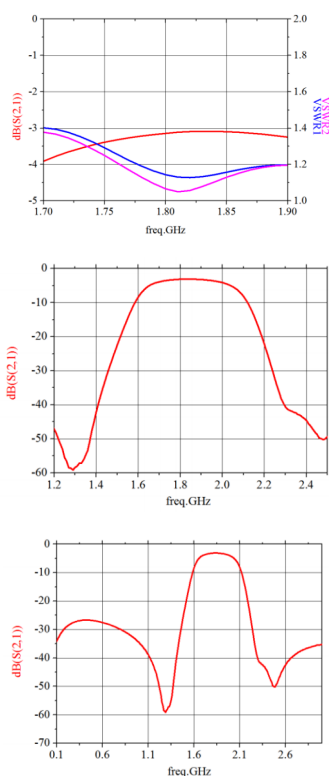


Size Code	Mini value (mm)	Nominal value (mm)	Max value (mm)
L	2.25	2.3	2.35
W	1.25	1.3	1.35
H1		0.65	
H2		0.65	

Assembly diagram



Typical test curve



Assembly instructions

1. Storage: The chip must be placed in a container with electrostatic protection function and stored in a nitrogen environment.
2. Electrostatic protection: Please strictly comply with ESD protection requirements to avoid electrostatic damage to devices.
3. Conventional operation: Avoid tool or finger contact with the chip surface during operation.
4. Mounting operation: Chip installation can be carried out using AuSn solder eutectic sintering process or conductive adhesive bonding process, and the mounting surface must be clean and flat.
5. Sintering process: Use AuSn solder with a gold tin ratio of 80/20. The temperature should not exceed 295 degrees, and the friction time should not exceed 3 seconds.
6. Bonding process: The amount of conductive adhesive should be minimized as much as possible. After placing the chip in the installation position, the conductive adhesive can be seen around it.
7. Bonding operation: Ball or wedge bonding uses 0.025mm gold wire and is carried out according to the general process.

Note: The specifications and performance data contained in this data sheet are based on tests established by CMW.